

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : Haujie CHEN, et al.

Group Art Unit: 2813

Appln. No. : 10/689,506

Examiner: J. M. Mitchell

Filed : October 20, 2003

For : HIGH PERFORMANCE STRESS-ENHANCED MOSFETs USING Si:C
AND SiGe EPITAXIAL SOURCE/DRAIN AND METHOD OF
MANUFACTURE

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
U.S. Patent and Trademark Office
Customer Service Window, Mail Stop Amendment
Randolph Building
401 Dulany Street
Alexandria, VA 22314
Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, and supplemental to the Information Disclosure Statement filed on August 31, 2005, applicant respectfully brings the following documents, listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application.

Further to the U.S. Patent and Trademark Office's decision to waive the requirement under 37 C.F.R. § 1.98 (a)(2)(i), copies of the U.S. patents and U.S. published patent applications are not enclosed herewith. However, if any copies are needed, the Examiner is respectfully requested to contact the undersigned. Copies of non-US patent documents as well as the documents listed in the "Other Documents" section of the attached PTO-1449 are enclosed.

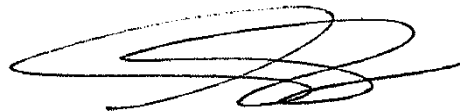
Applicants respectfully request that the Examiner consider the materials cited and indicate such consideration by appropriately initialing the enclosed PTO-1449 Form and including a copy of the initialed form in the next official communication.

Applicants note that this Information Disclosure Statement is being after receipt of a first action on the merits from the U.S. Patent and Trademark Office. Accordingly, please charge the required fee of \$180.00 to **IBM Deposit Account No. 09-0458**.

Should the US Patent & Trademark Office conclude that other fees are required, authorization is hereby given to charge **IBM Deposit Account No. 09-0458** any fee necessary to ensure consideration of these materials.

Should there be any questions concerning this application, the Examiner is invited to contact the undersigned at the below listed telephone number.

Respectfully submitted,
Haujie CHEN, et al.



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May 15, 2006
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FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030241US1		Application No. 10/689,506	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Huajie CHEN, et al..			
				Filing Date 10/20/2003		Group 2813	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
		JP 64-76755	3-22-1989	Japan			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER				DATE CONSIDERED			
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030241US1	Application No. 10/689,506		
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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
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		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.					
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